

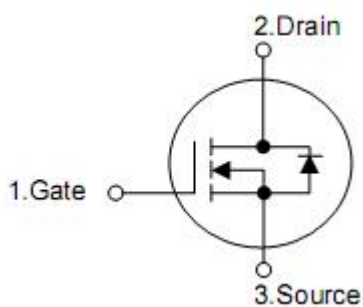
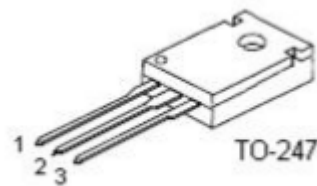
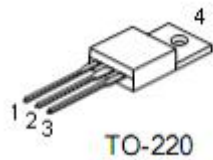
1. Applications

- n Power supply
- n DC-DC converters

2. Features

- n $R_{DS(on)} = 7m\Omega @V_{GS} = 10 V$
- n Lead free and Green device available
- n Low RDS-on to minimize conductive loss
- n High avalanche current

3. Pin configuration



Pin	Function
1	Gate
2	Drain
3	Source
4	Drain

4. Absolute maximum ratings

(T_C= 25°C , unless otherwise specified)

Parameter	Symbol	Rating		Units
		TO-220	TO-247	
Drain-source voltage	V _{DSS}	60		V
Gate-source voltage	V _{GSS}	±25		V
Continuous Drain Current	T _C =25 °C	80		A
	T _C =100 °C	60		
Pulsed Drain Current	T _C =25 °C	300		
Avalanche Current	I _{AS} ⁵	21.5		
Avalanche Energy	E _{AS} ⁵	462.25		mJ
Maximum Power Dissipation	T _C =25 °C	183	215	W
	T _C =100 °C	92	107.5	
Junction & Storage Temperature Range	T _L , T _{STG}	-55~+175		°C

5. Thermal characteristics

Symbol	Parameter	Typical		Unit
		TO-220	TO-247	
R _{θJC}	Thermal Resistance, Junction-to-Case	0.68	0.58	°C /W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	62.5		

6. Electrical characteristics

(T_J=25°C, unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	60	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =48V, V _{GS} =0V T _J =125 °C	-	-	1	μA
			-	-	100	μA
Gate-body leakage current	I _{GSS}	V _{GS} =+25V, V _{DS} =0V	-	-	+100	nA
		V _{GS} =-25V, V _{DS} =0V	-	-	-100	nA
On characteristics						
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0	3.0	4.0	V
Drain-source on resistance	R _{DS(on)} ¹	V _{GS} =10V, I _D =30A	-	7	8.5	mΩ
Dynamic Characteristics²						
Input capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1MHz	-	3390	-	pF
Output capacitance	C _{oss}		-	371	-	
Reverse transfer capacitance	C _{rss}		-	258	-	
Gate Repacitance	R _G	V _{GS} =0V, V _{DS} =0V, F=1.0MHz	-	1.8	-	Ω
Total gate charge	Q _g	V _{DS} =30V, I _D =30A, V _{GS} =10V,	-	73	-	nC
Gate-source charge	Q _{gs}		-	18	-	
Gate-drain charge	Q _{gd}		-	22	-	
Resistive swiching characteristics ²						
Turn-on delay time	t _{d(ON)}	V _{DD} =30V, I _D =30A, V _{GS} =10V R _G =6.8Ω	-	18	-	ns
Rise time	t _{rise}		-	120	-	
Turn-off delay time	t _{d(OFF)}		-	55	-	
Fall time	t _{fall}		-	68	-	
Diode Characteristics						
Diode Forward Voltage	V _{SD} ¹	V _{GS} =0V, I _{SD} =20A	-	-	1.3	V
Diode Continuous Forwardcurrent	I _S ³		-	-	114	A
Reverse recovery time	t _{rr}	I _F =30A, di/dt=100A/μs	-	45	-	ns
Reverse recovery charge	Q _{rr}		-	76	-	nC

Note:

1: Pulse test; pulse width ≤ 300us, duty cycle ≤ 2%.

2: Guaranteed by design, not subject to production testing.

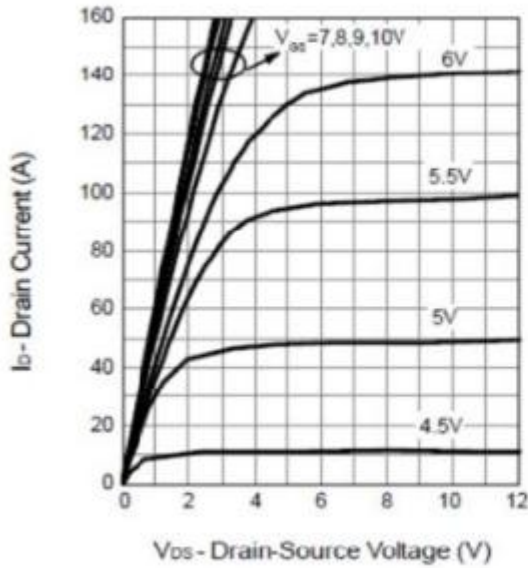
3: Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 55A.

4: Repetitive rating, pulse width limited by max junction temperature.

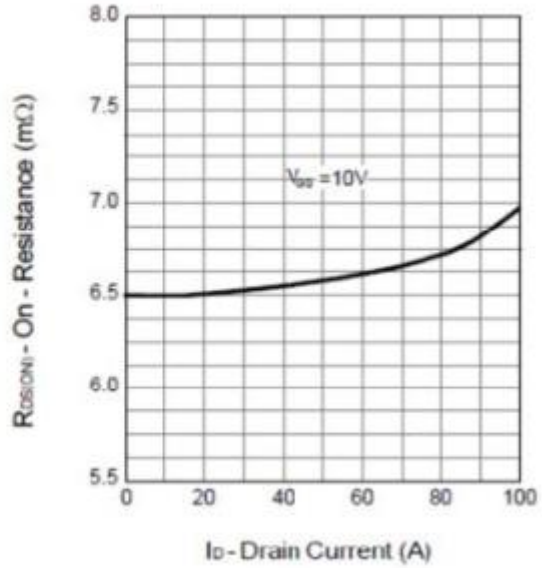
5: Starting T_J=25 °C, V_D=50V, L=0.5mH, I_{AS} =43A.

7. Typical Characteristics

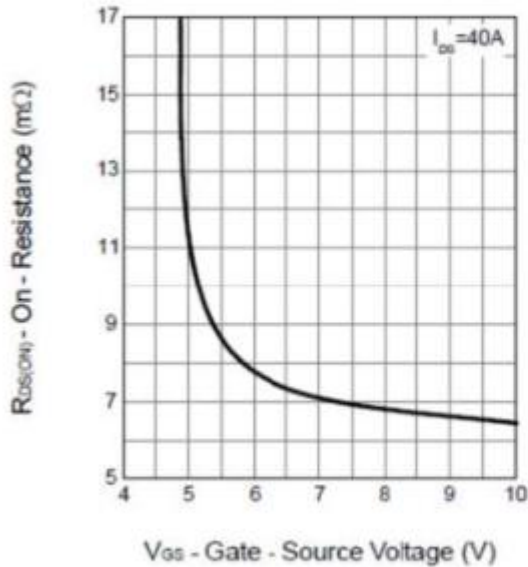
Output Characteristics



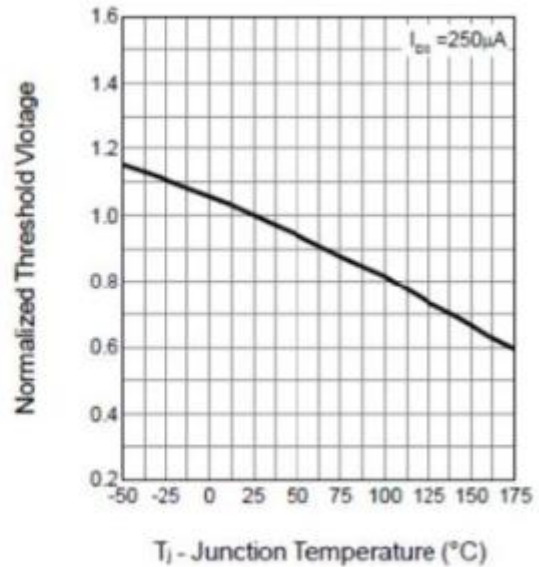
Drain-Source On Resistance



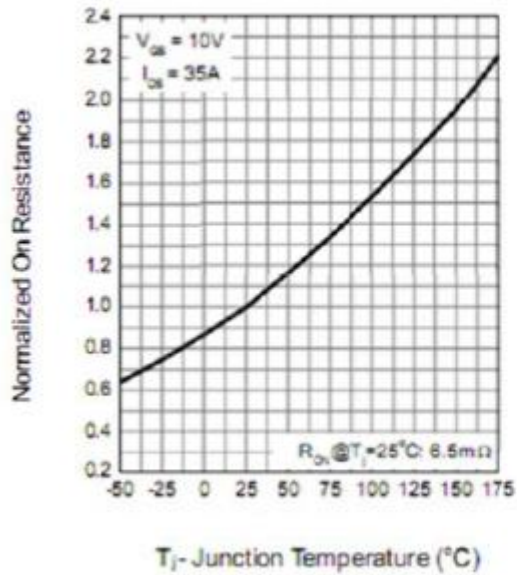
Drain-Source On Resistance



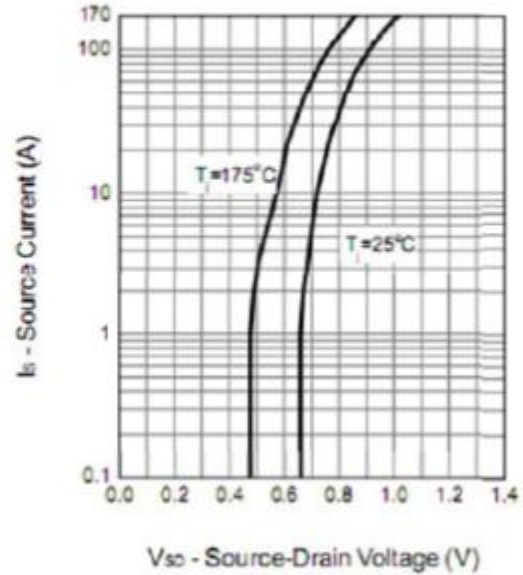
Gate Threshold Voltage



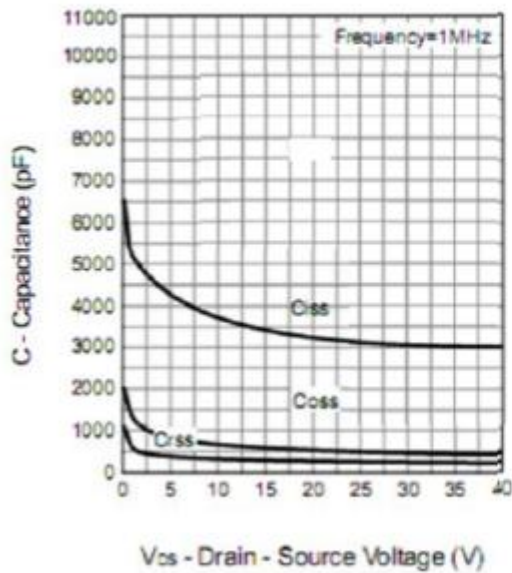
Drain-Source On Resistance



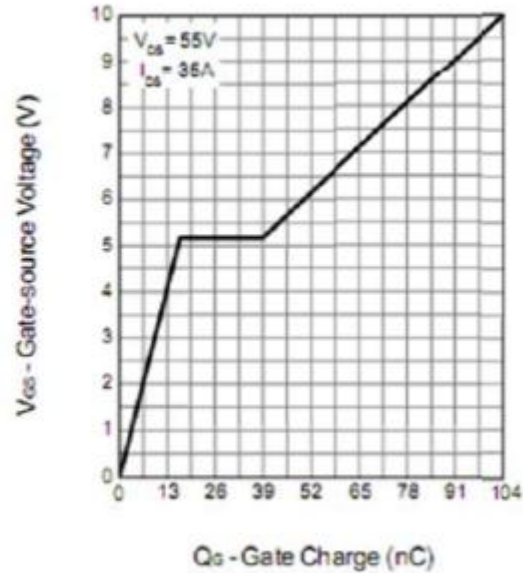
Source-Drain Diode Forward



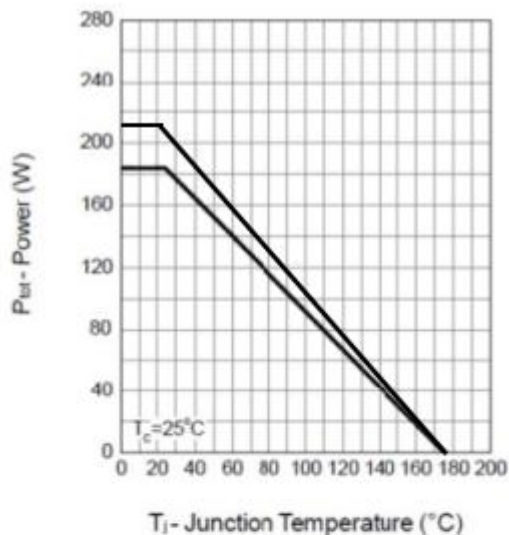
Capacitance



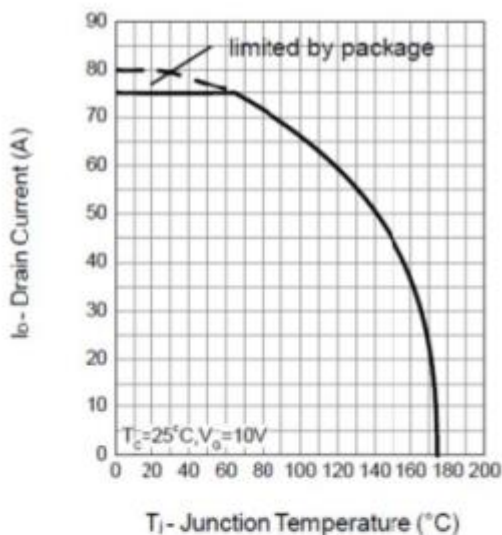
Gate Charge



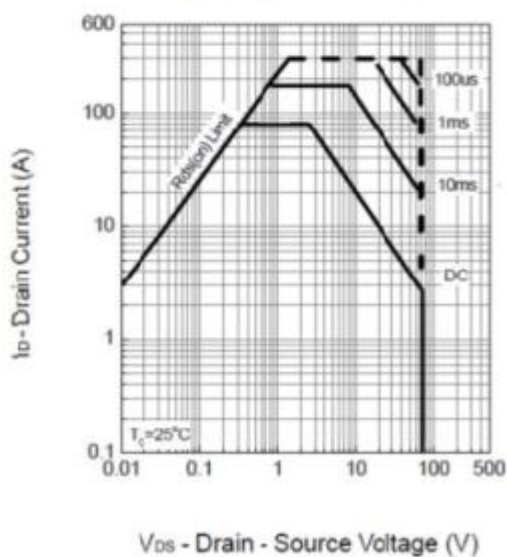
Power Dissipation



Drain Current



Safe Operation Area



Thermal Transient Impedance

